

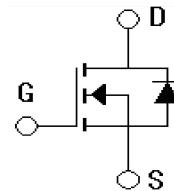
Features

- Low gate charge
- Low Crss (Typical 82pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product



Applications

- High efficiency switch mode power supplies
- Electronic lamp ballasts based on half bridge
- UPS



Absolute Ratings (Tc=25°C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	250	V
Drain Current -continuous	I _D , T=25°C	40	A
	T=100°C	25	A
Drain Current - pulse (note1)	I _{DM}	160	A
Gate-Source Voltage	V _{GSS}	±30	V
Single Pulsed Avalanche Energy (note 2)	E _{AS}	880	mJ
Power Dissipation	PD	158	W
	TC=25°C	1.265	W/°C
Operating and Storage Temperature Range	T _j , T _{STG}	-55~+150	°C
Maximum Lead Temperature for Soldering Purposes	T _L	300	°C

*Drain current limited by maximum junction temperature

Electrical Characteristics (T_{CASE}=25°C unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Type	Max	Units
Off-Characteristics						
Drain-Source Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	250	-	-	V
Drain cut-off current	I _{DSS}	V _{DS} =250V, V _{GS} =0V	-	-	1	μA
		T _j =25°C	-	-	10	
Gate-body leakage current,forward	I _{GSSF}	V _{DS} =0V, V _{GS} =30V	-	-	100	nA
Gate-body leakage	I _{GSSR}	V _{DS} =0V, V _{GS} =-30V	-	-	-100	nA

current,reverse							
On-Characteristics							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V	
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=1A$	-	-	94	$m\Omega$	
Forward Transconductance	g_{fs}	$V_{DS} = 40V, I_D=20A$ (note4)	-	27	-	S	
Dynamic Characteristics							
Input capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$ (Note 4)	-	3300	4000	pF	
Output capacitance	C_{oss}		-	650	800	pF	
Reverse transfer capacitance	C_{rss}		-	82	105	pF	
Switching Characteristics							
Turn-On delay time	$t_{d(on)}$	$V_{DD}=125V, I_D=40A, R_G=25\Omega, V_{GS}=10V$ (Note 4,5)	-	80	115	ns	
Turn-On rise time	t_r		-	600	930	ns	
Turn-Off delay time	$t_{d(off)}$		-	145	185	ns	
Turn-Off Fall time	t_f		-	180	234	ns	
Total Gate Charge	Q_g	$V_{DS}=200V, I_D=40A, V_{GS}=10V$ (note 4,5)	-	87	110	nC	
Gate-Source charge	Q_{gs}		-	25	-	nC	
Gate-Drain charge	Q_{gd}		-	42	-	nC	
Drain-Source Diode Characteristics and Maximum Ratings							
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=40A$ (note3)	-	-	1.5	V	
Maximum Continuous Drain-Source Diode Forward Current		I_S	-	-	40	A	
Reverse recovery time	t_{rr}	$V_{GS}=0V, I_F=40A$ $dI/dt=100A/\mu s$ (note 4)	-	210	-	ns	
Reverse recovery charge	Q_{rr}		-	2.1	-	μC	

Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.79	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}C/W$

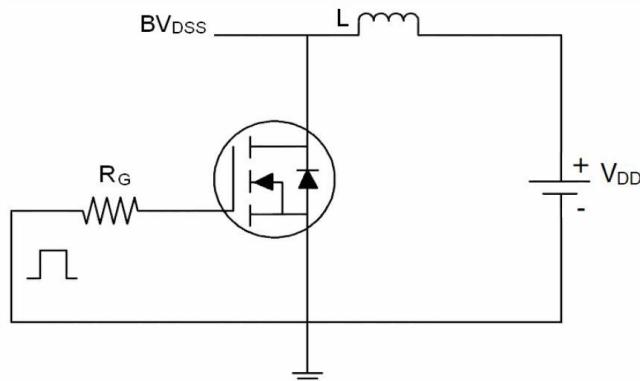
Notes:

1. Pulse width limited by maximum junction temperature
2. $L=1.1mH, I_{AS}=40A, V_{DD}=50V, R_G=25 \Omega$, Starting $T_J=25^{\circ}C$
3. $ISD \leq 40A, di/dt \leq 200A/\mu s, V_{DD} \leq BVDSS$, Starting $T_J=25^{\circ}C$
4. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

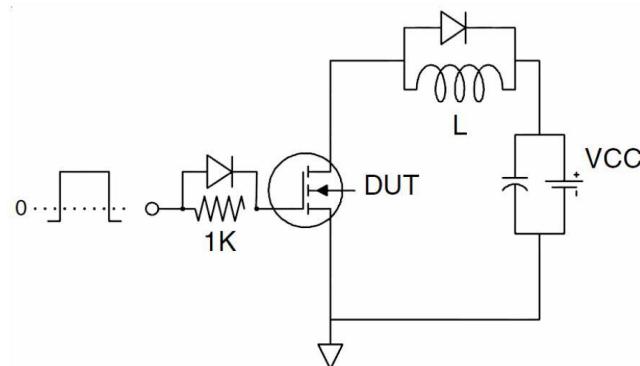
5. Essentially independent of operating temperature

Test Circuit

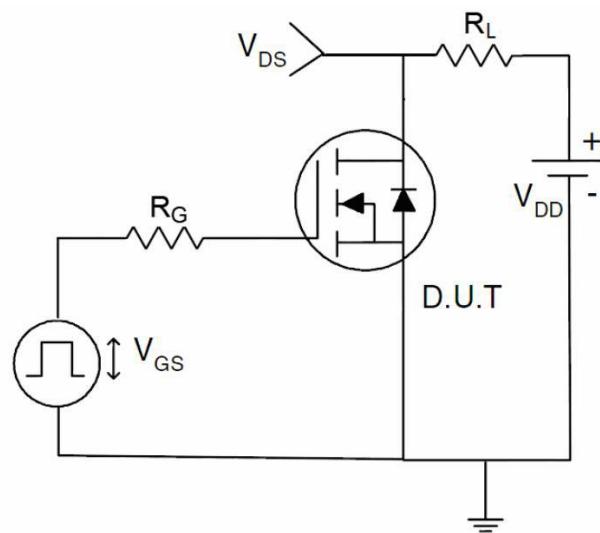
1) E_{AS} test Circuit



2) Gate charge test Circuit

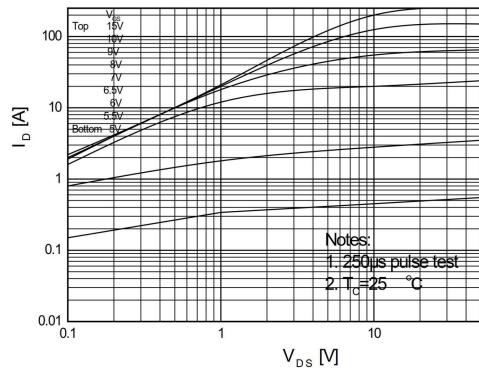


3) Switch Time Test Circuit

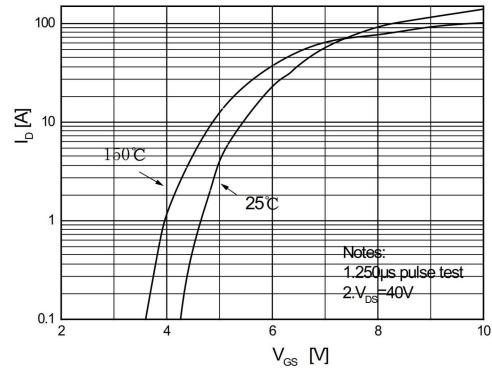


Typical Electrical and Thermal Characteristics (Curves)

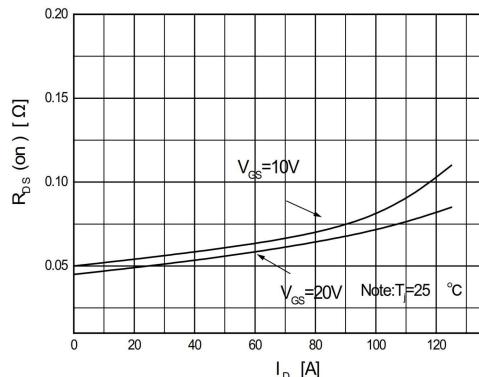
On-Region Characteristics



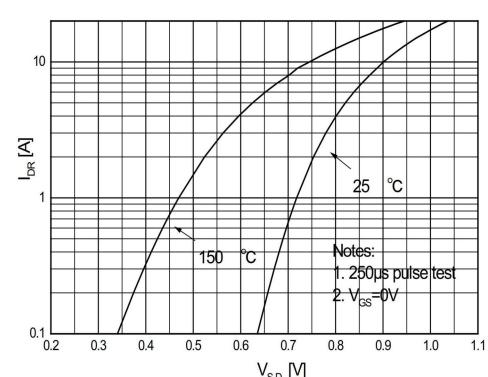
Transfer Characteristics



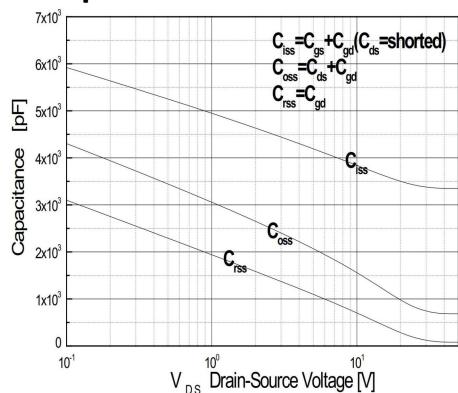
On-Resistance Variation vs. Drain Current and Gate Voltage



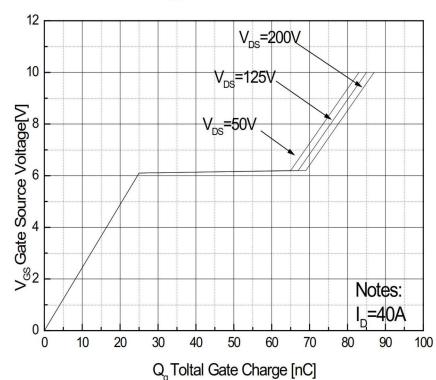
Body Diode Forward Voltage Variation vs. Source Current and



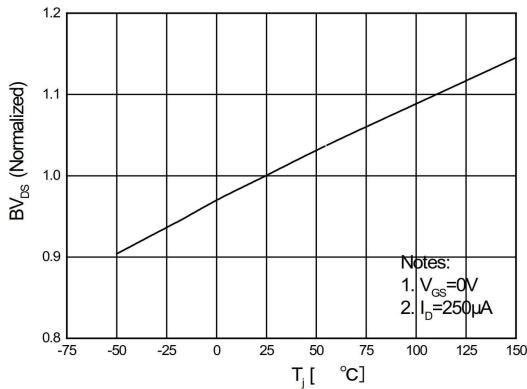
Capacitance Characteristics



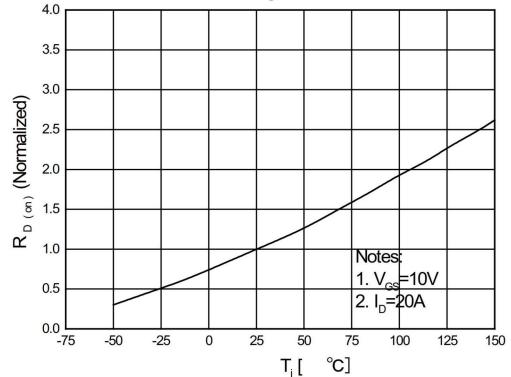
Gate Charge Characteristics



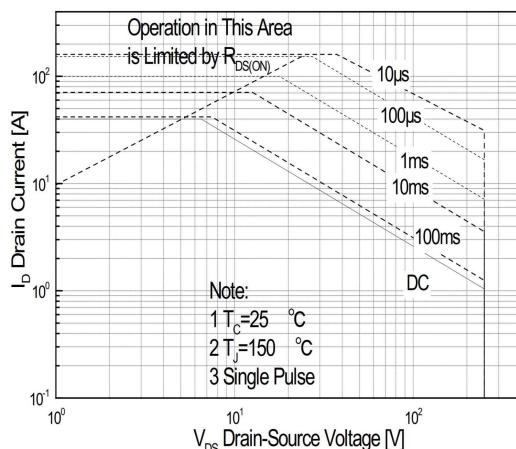
Breakdown Voltage Variation vs.Temperature



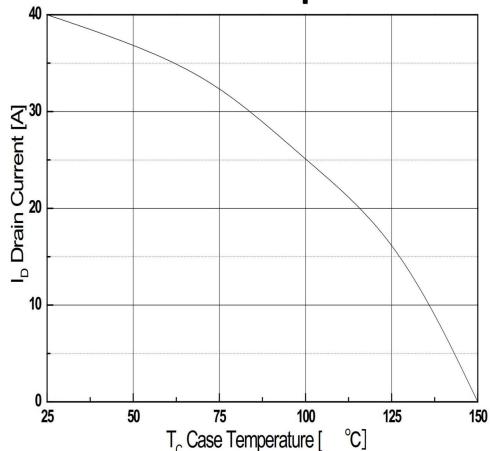
On-Resistance Variation vs.Temperature



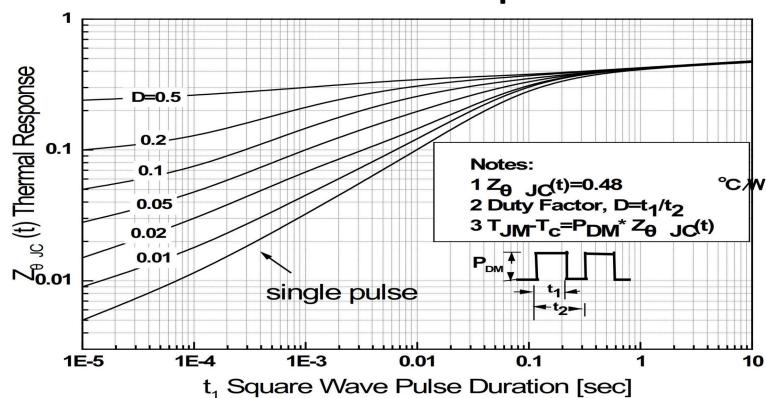
Maximum Safe Operating Area



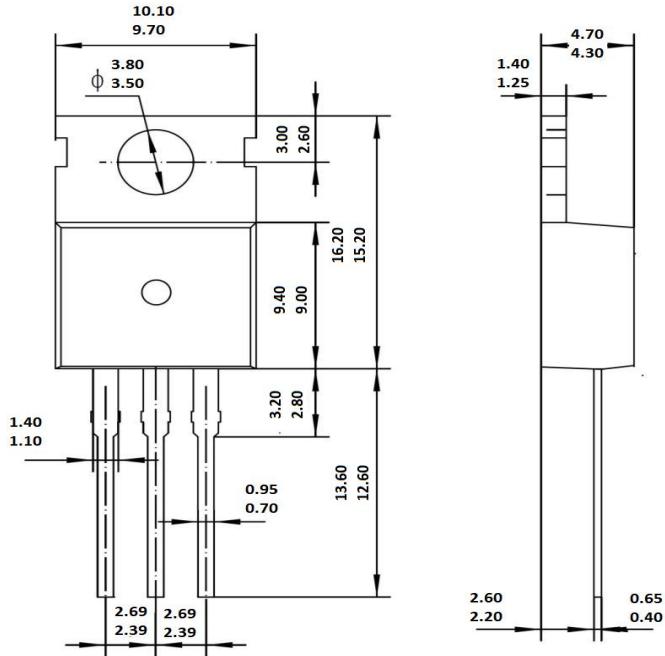
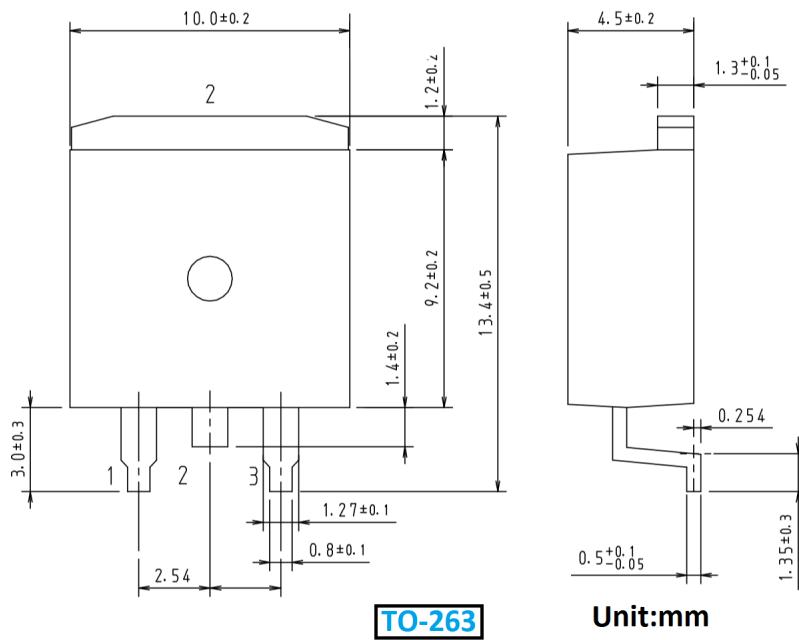
Maximum Drain Current vs.Case Temperature



Transient Thermal Response Curve



Package Mechanical DATA

**TO-220****Unit: mm****TO-263****Unit:mm**